

abstract

In the present work , schottky photodiode have been mode on n-type SiC by depositing of thin layer of In . electrical characteristics included I-V (dark and illumination ) have been investigated . Ideality factor is 1.6 and barrier height is 0.53 eV was calculated from I-V and Isc-Voc characteristics, Ideality factor is 1.7 and barrier height found to be 0.64 eV, and from optoelectronic characteristics have found sensitivity results show that peak response of photodiode was 550nm . Keyword: photodiode,SiC,Schottky contact,